

Serial No: 10/692,938
Examiner: H. Trinh
Title: SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

Amendments to the Specification:

Please replace the paragraph beginning on line 12 on page 6 with the following amended paragraph:

[[(2) Ultrasonic diffusion]] (2) Ultrasonic bonding

By bringing the metal layer of the electrode and the metal layer of the electrode-part-connection electrode into contact with each other and applying ultrasonic wave to them, a contamination layer present at interfaces between the metal layer of the electrode part and the metal layer of the electrode-part-connection electrode is decomposed finely by repetitive sliding and expansion. The decomposed contamination layer is taken into metallic crystals of each metal layer, whereby a bonding structure in which the electrode part and the electrode-part-connection electrode are connected by metal joint is obtained.

Please replace the paragraph beginning on line 22 on page 6 with the following amended paragraph:

[[(3) Room temperature diffusion]] (3) Room temperature bonding

If the metal layer of the electrode part and the metal layer of the electrode-part-connection electrode are brought into contact with each other in a state in which surfaces of the metal layer of the electrode part and the metal layer of the electrode-part-connection electrode are cleaned (oxide films and contamination layers are removed), a bonding structure in which the metal layer of the electrode part and the metal layer of the electrode-part-connection electrode are bonded by the intermolecular force is obtained.